



### **40V P-Channel Enhancement Mode MOSFET**

Voltage

-40 V

Current

-50 A

### **Features**

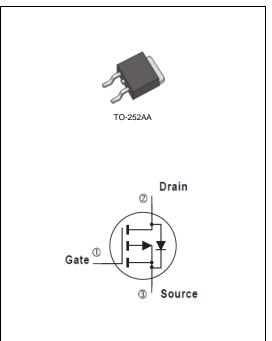
- $R_{DS(ON)}$ ,  $V_{GS}$ @-10V,  $I_{D}$ @-10A<12m $\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}@-4.5V$ ,  $I_D@-8A<17.5m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

• Case: TO-252AA Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0104 ounces, 0.297grams



## Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	-40	.,	
Gate-Source Voltage		$V_{GS}$	<u>+</u> 20	V	
Continuous Drain Current (Note 4)	T <sub>C</sub> =25°C	l <sub>D</sub>	-50	А	
	T <sub>C</sub> =100°C		-32		
Pulsed Drain Current (Note 1)	T <sub>C</sub> =25°C	I <sub>DM</sub>	-166	ļ	
Power Dissipation	T <sub>C</sub> =25°C	Po	63	10/	
	T <sub>C</sub> =100°C		25	W	
Continuous Drain Current (Note 4)	T <sub>A</sub> =25°C	I <sub>D</sub>	-9	^	
	T <sub>A</sub> =70°C		-7	A	
Power Dissipation	T <sub>A</sub> =25°C	Po	2	10/	
	T <sub>A</sub> =70°C		1.3	W	
Operating Junction and Storage Temperature Range		$T_{J}$ , $T_{STG}$	-55~150	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{\theta JC}$	2	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

• Limited only By Maximum Junction Temperature





## **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static			•	•	•	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	$V_{GS} = 0V, I_{D} = -250uA$		-	-	- <sub>V</sub>
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=-250uA$	-1	-1.52	-2.5	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-10A	-	10	12	mΩ
		$V_{GS}$ =-4.5V, $I_{D}$ =-8A	-	13.5	17.5	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-40V, V <sub>GS</sub> =0V	-	-	-1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 6)						
Total Gate Charge	$Q_{g}$	V <sub>DS</sub> =-32V, I <sub>D</sub> =-10A, V <sub>GS</sub> =-4.5V <sup>(Note 2,3)</sup>	-	23	-	nC
Gate-Source Charge	$Q_gs$		-	8.5	-	
Gate-Drain Charge	$Q_gd$		-	9	-	
Input Capacitance	Ciss	V <sub>DS</sub> =-25V, V <sub>GS</sub> =0V, f=1MHZ	-	2767	-	pF
Output Capacitance	Coss		-	247	-	
Reverse Transfer Capacitance	Crss	I=IIVIMZ	-	139	-	
Turn-On Delay Time	td <sub>(on)</sub>	$V_{DS}$ =-20V, $I_{D}$ =-1A, $V_{GS}$ =-10V, $R_{G}$ =6 $\Omega$ (Note 2,3)	-	23	-	ns
Turn-On Rise Time	t <sub>r</sub>		-	10	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	135	-	
Turn-Off Fall Time	t <sub>f</sub>		-	50	-	
Drain-Source Diode						
Maximum Continuous Drain-Source				-	-50	А
Diode Forward Current	I <sub>S</sub>		_			
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-1A, V <sub>GS</sub> =0V	-	-0.7	-1	V

#### NOTES:

- Pulse width
   2300us, Duty cycle
   2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial  $T_J$  =25°C.
- 4. The maximum current rating is package limited.
- 5. Roja is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.





#### TYPICAL CHARACTERISTIC CURVES

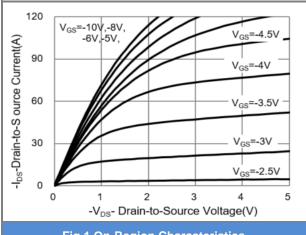
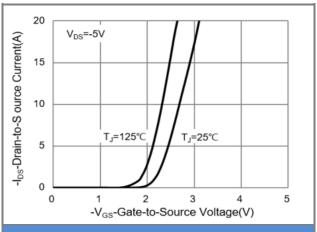


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

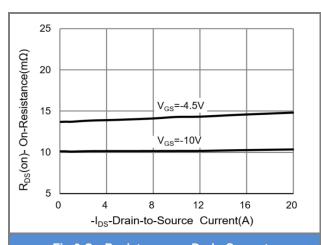


Fig.3 On-Resistance vs. Drain Current

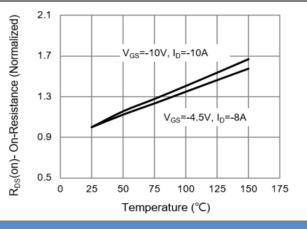


Fig.4 On-Resistance vs. Junction temperature

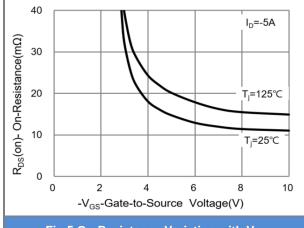
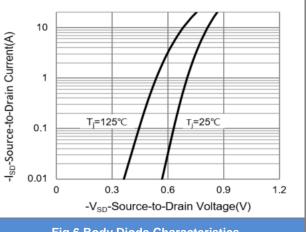


Fig.5 On-Resistance Variation with V<sub>GS</sub>



**Fig.6 Body Diode Characteristics** 





#### TYPICAL CHARACTERISTIC CURVES

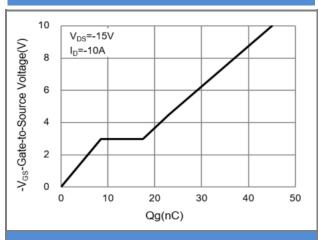


Fig.7 Gate-Charge Characteristics

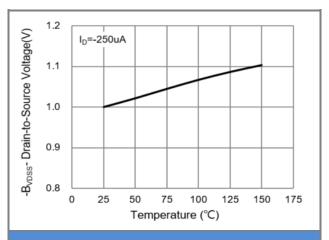


Fig.8 Breakdown Voltage Variation vs. Temperature

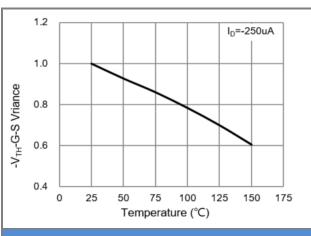


Fig.9 Threshold Voltage Variation with Temperature

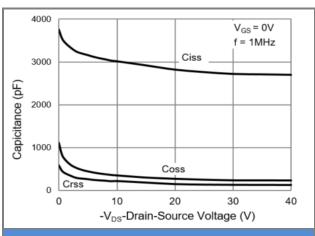
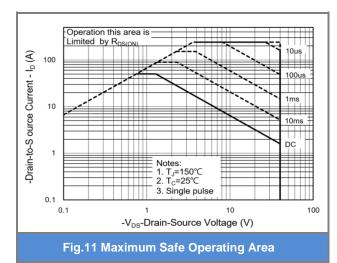
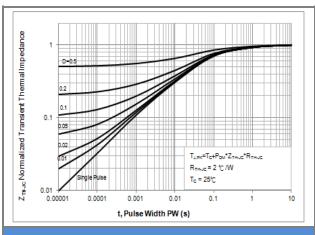


Fig.10 Capacitance vs. Drain-Source Voltage





**Fig.12 Normalized Thermal Transient Impedance** 

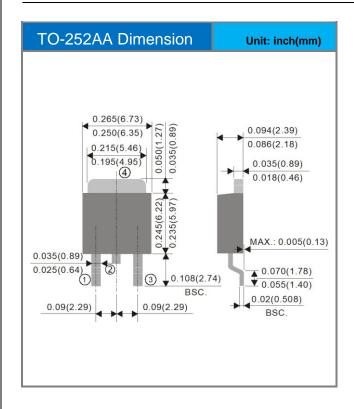


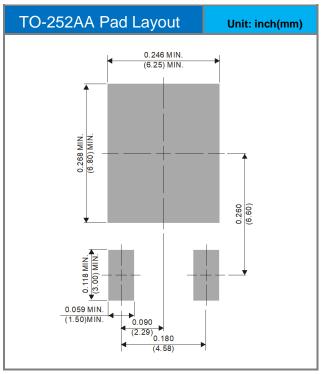


### **Part No Packing Code Version**

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJD50P04-AU_L2_000A1	TO-252AA	3,000pcs / 13" reel	D50P04	Halogen free

## **Packaging Information & Mounting Pad Layout**









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